

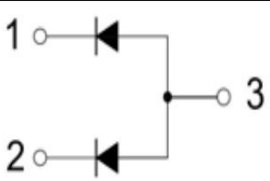
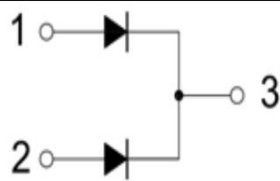
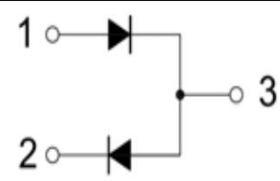
SOT-23 Plastic-Encapsulate Diodes

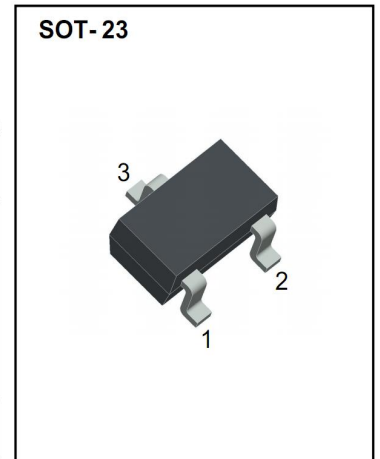
BAW56/BAV70/BAV99

Switching Diodes

FEATURES:

- High Conductance
- Fast Switching Speed
- For General Purpose Switching Applications

BAW56	BAV70	BAV99
		
MARKING:A1	MARKING A4	MARKING:A7



Solid dot = Green molding compound device, if none, the normal device.

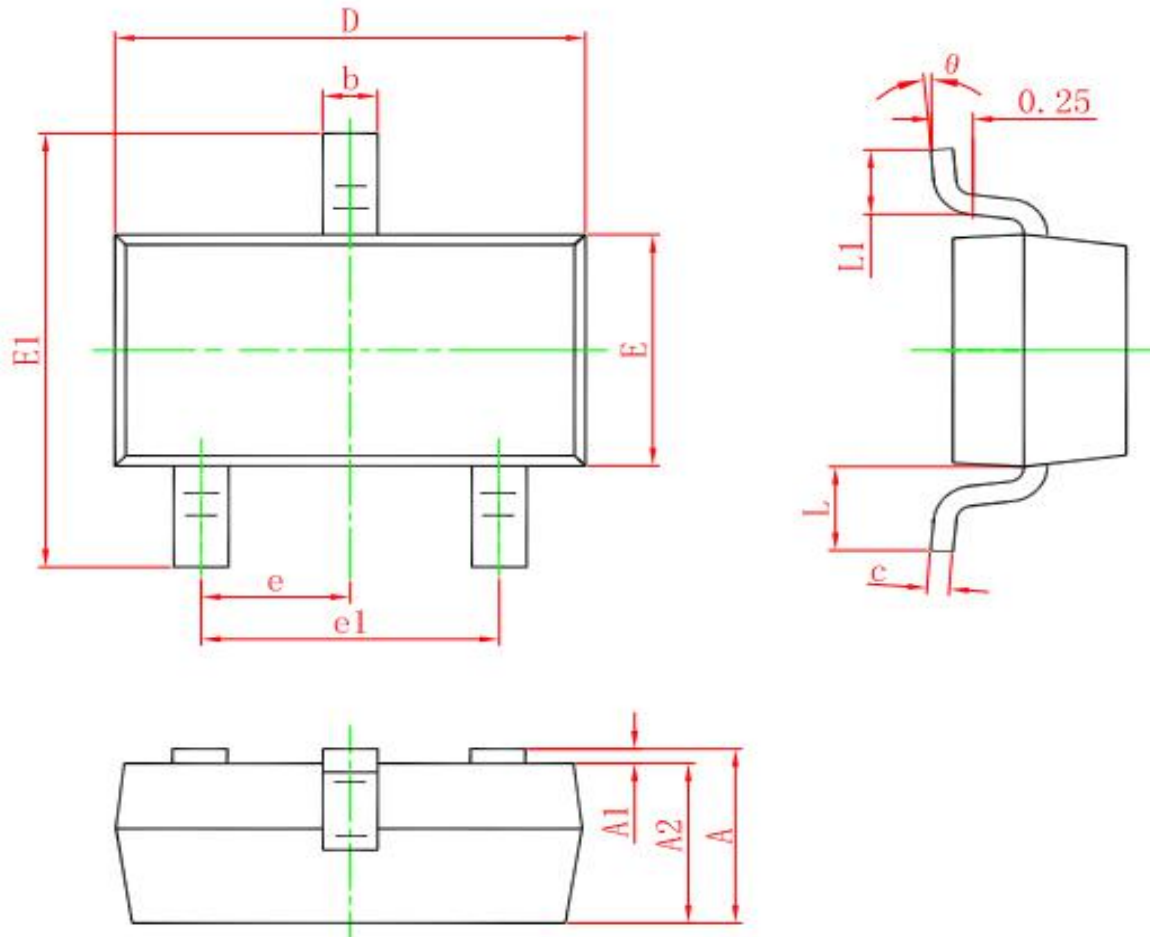
Maximum ratings (@Ta=25°C)

Parameter	Symbol	Limit	Unit
Reverse Voltage	VR	70	V
Forward Current	IF	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	225	mW
Thermal Resistance from Junction to Ambient	RθJA	556	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55~+150	°C

Electrical Characteristics (@Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)	IR=100μA	70			V
Forward voltage	VF1	IF=1mA			0.715	V
	VF2	IF=10mA			0.855	V
	VF3	IF=50mA			1	V
	VF4	IF=150mA			1.25	V
Reverse current	IR	VR=70V			2.5	uA
capacitance Between terminals	Ctot	VR=0V, f=1MHz			1.5	PF
Reverse recovery time	t _{rr}	IF=IR=10mA, Irr=0.1×IR, RL= 100 Ω			6	nS

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°